

672nd ASRC Seminar

Date: Thursday, March 30, 13:30 ~ 15:00

Location: Room 103, ASRC bldg.

Speaker: Professor Koichiro Saiki
(The University of Tokyo)

Title: Synthesis of graphene –chemical vapor deposition and graphene oxide

Abstract: Graphene, a monolayer sheet of graphite, has various attractive properties such as high carrier mobility, mechanical strength, flexibility, and optical transparency. Considering industrial applications, development of a high through-put method for fabricating graphene is required. Among various methods, a chemical route such as chemical vapor deposition (CVD) and chemical exfoliation of graphite is considered to be promising. There are, however, several problems to be solved before practical application. We have investigated physical and chemical processes in CVD growth of graphene and reduction of chemically exfoliated graphene oxide (GO). In this talk, I would like to introduce our recent results on real-time observation of CVD growth of graphene and plasma enhanced high-degree reduction of GO, which are aiming at the growth of a large-area and single-crystalline graphene.

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